

RB751V-40

Silicon Epitaxial Planar Schottky Barrier Diode

Features

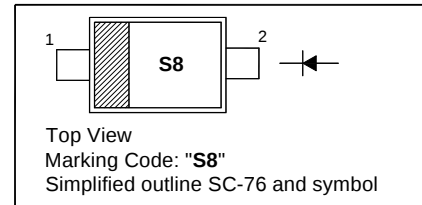
- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability

Applications

- High speed switching

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



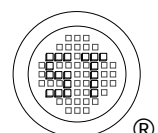
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

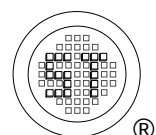
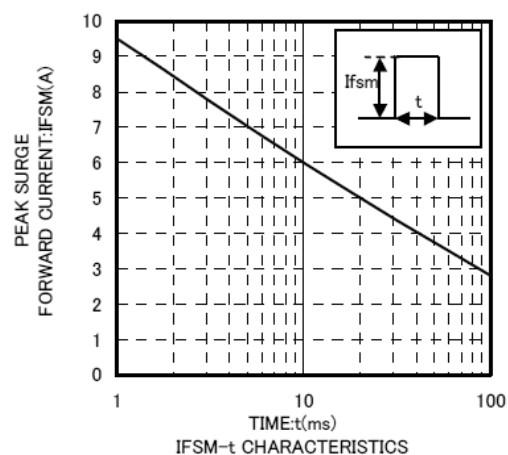
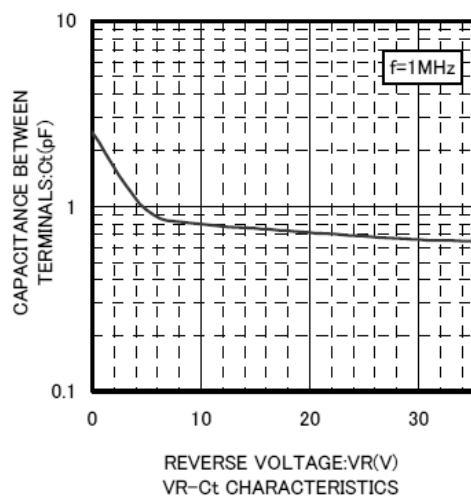
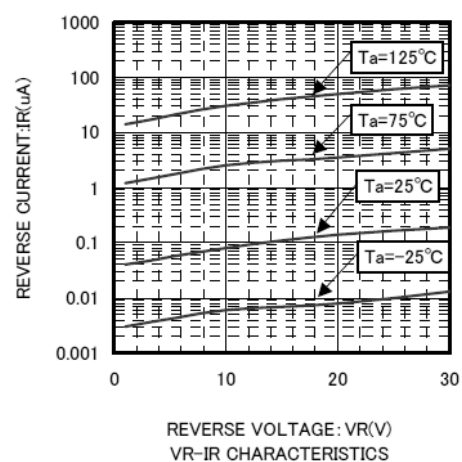
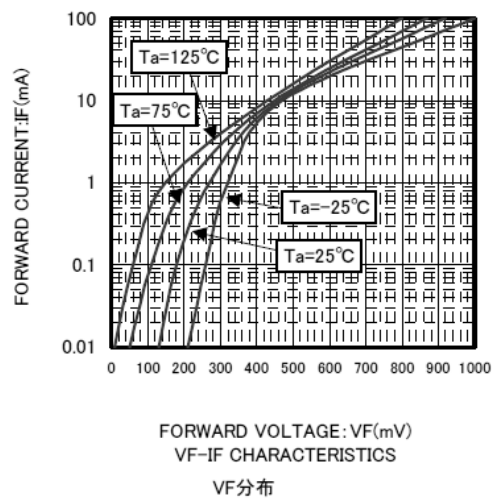
Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	40	V
Reverse Voltage	V_R	30	V
Average Forward Rectifying Current	$I_{F(AV)}$	30	mA
Peak Forward Surge Current (60 Hz for 1 Cyc.)	I_{FSM}	200	mA
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 40 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 1\text{ mA}$	V_F	-	0.37	V
Reverse Current at $V_R = 30\text{ V}$	I_R	-	0.5	μA
Capacitance Between Terminals at $V_R = 1\text{ V}$, $f = 1\text{ MHz}$	C_T	2	-	pF

Note: ESD sensitive product handling required.

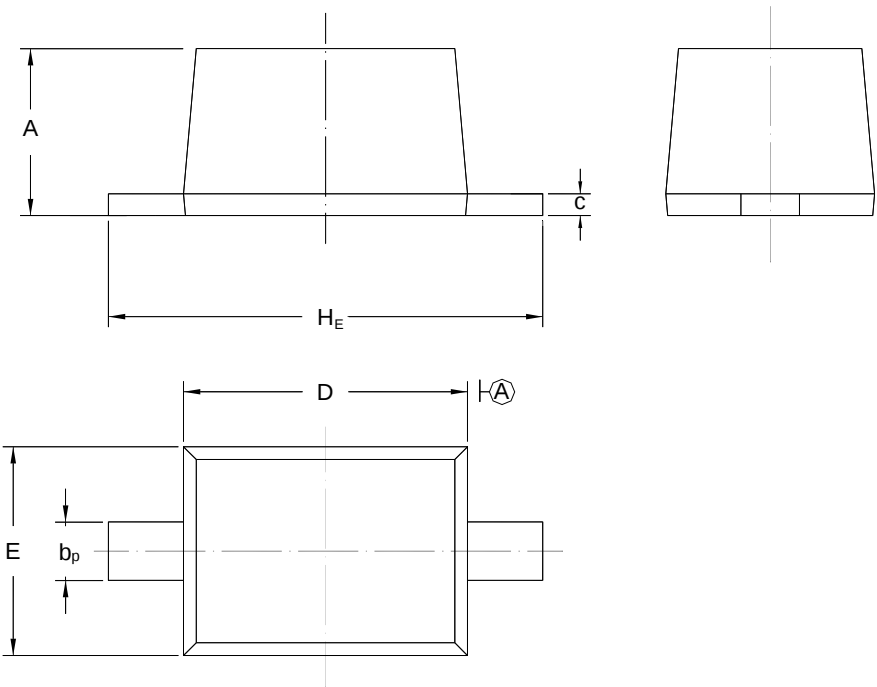




PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SC-76



UNIT	A	b_p	C	D	E	H_E
mm	1.10 0.80	0.40 0.25	0.15 0.10	1.80 1.60	1.35 1.15	2.80 2.30

